

ABSTRACT OF THE DISCLOSURE

The present invention provides a method of treating a surface of
5 a semiconductor substrate, the surface of the semiconductor substrate
including at least any one of a copper region, a copper based region and a
copper alloy region, the method comprises the steps of : carrying out an
anti-corrosion treatment by exposing the surface of the semiconductor
substrate to a solution containing an anti-corrosive agent ; and forming a
10 copper-diffusion stopper insulating film over the surface of the
semiconductor substrate.